

Silicon NPN Power Transistors

2SD762 2SD762A

DESCRIPTION

www.datasheet4u.com

- With TO-220C package
- Wide area of safe operation

APPLICATIONS

- For audio frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

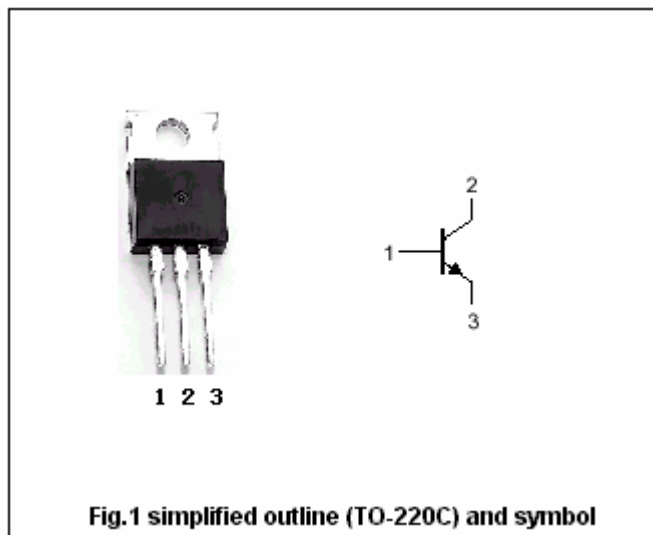


Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings(Tc=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2SD762	60	V
		2SD762A	80	
V _{CEO}	Collector-emitter voltage	2SD762	60	V
		2SD762A	80	
V _{EBO}	Emitter-base voltage	Open collector	8	V
I _C	Collector current		4	A
I _{CM}	Collector current-peak		6	A
I _B	Base current		1	A
P _C	Collector power dissipation	T _C =25°C	30	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2SD762	I _C =0.2A; L=25mH	60			V
		2SD762A		80			
V _{CEsat}	Collector-emitter saturation voltage	I _C =2 A; I _B =0.4 A			1.0	V	
V _{BE}	Base-emitter on voltage	I _C =1A ; V _{CE} =3V			1.2	V	
I _{CBO}	Collector cut-off current	V _{CB} =50V; I _E =0			30	μA	
I _{EBO}	Emitter cut-off current	V _{EB} =8V; I _C =0			1	mA	
h _{FE-1}	DC current gain	I _C =0.1A ; V _{CE} =3V	40				
h _{FE-2}	DC current gain	I _C =1A ; V _{CE} =3V	30		160		

◆ h_{FE-2} classifications

Q	P	O
30-60	50-100	80-160

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PACKAGE OUTLINE

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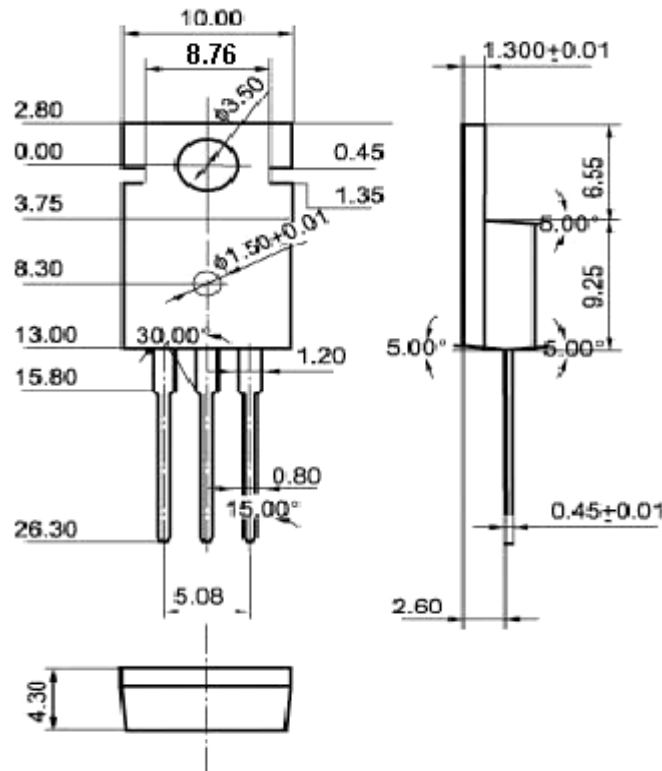


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)